

# **ISC Silicon NPN Power Transistor**

#### **DESCRIPTION**

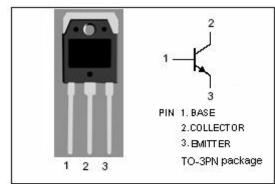
- Collector-Emitter Sustaining Voltage-V<sub>CEO(SUS)</sub>= 800V(Min)
- · High Speed Switching
- Good Linearity of hFE
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

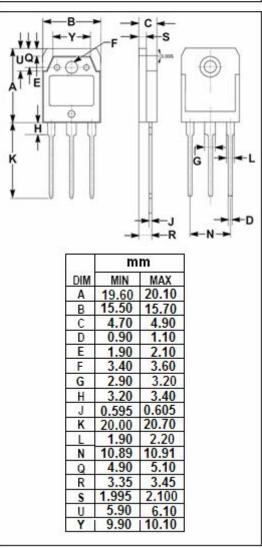
### **APPLICATIONS**

Designed for power switching applications

# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	1000	V	
V <sub>CES</sub>	Collector-Emitter Voltage	1000	٧	
Vceo	Collector-Emitter Voltage	800	V	
$V_{EBO}$	Emitter-Base Voltage 7		٧	
Ic	Collector Current-Continuous	3	Α	
I <sub>CM</sub>	Collector Current-Peak	6	А	
I <sub>B</sub>	Base Current-Continuous	2 A		
Pc	Collector Power Dissipation @ Tc=25°C	70	W	
	Collector Power Dissipation @ T <sub>a</sub> =25°C	2.5		
TJ	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$	







# isc Silicon NPN Power Transistor

2SC3285

### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> =1mA; I <sub>B</sub> = 0	800			V			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.4A			1.5	V			
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.4A			1.5	V			
І <sub>СВО</sub>	Collector Cutoff Current	V <sub>CB</sub> = 1000V; I <sub>E</sub> = 0			50	μА			
І <sub>ЕВО</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			50	μА			
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 2A; V <sub>CE</sub> = 5V	6						
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 5V; f= 1MHz		4		MHz			
Switching Times									
ton	Turn-on Time				1.0	μ \$			
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 2A, I <sub>B1</sub> = 0.4A; I <sub>B2</sub> = -0.8A, V <sub>CC</sub> = 250V			2.5	μ \$			
t <sub>f</sub>	Fall Time				0.5	μS			

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